

N-Channel 120 V (D-S) MOSFET



RoHS
COMPLIANT

PRODUCT SUMMARY

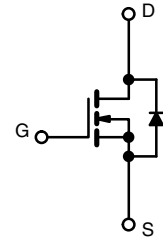
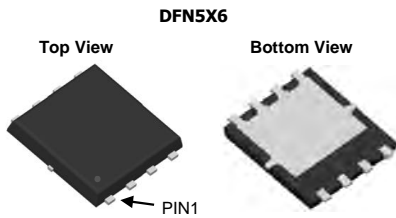
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^{a, d} | Q_g (Typ.) |
|--------------|---------------------------|---------------------------|--------------|
| 120 | 0.008 at $V_{GS} = 10$ V | 85 | 79nC |

FEATURES

- TrenchFET IIPower MOSFET
- 100 % Rgand UIS Tested

APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converters
- OR-ing
- Power supplies
- Motor drive control
- Battery and load switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|---|----------------|---------------|----------------------|
| Drain-source voltage | V_{DS} | 120 | V |
| Gate-source voltage | V_{GS} | ± 20 | |
| Continuous drain current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | 85 ^a |
| | | $T_C = 70$ °C | 66.1 |
| | | $T_A = 25$ °C | 20.8 ^{b, c} |
| | | $T_A = 70$ °C | 9.5 ^{b, c} |
| Pulsed drain current ($t = 100$ μ s) | I_{DM} | 340 | A |
| Continuous source-drain diode current | I_S | $T_C = 25$ °C | 85 ^a |
| | | $T_A = 25$ °C | 5.6 ^{b, c} |
| Single pulse avalanche current | I_{AS} | 70 | |
| Single pulse avalanche energy | E_{AS} | 103 | mJ |
| Maximum power dissipation | P_D | $T_C = 25$ °C | 155 |
| | | $T_C = 70$ °C | 93 |
| | | $T_A = 25$ °C | 5.15 ^{b, c} |
| | | $T_A = 70$ °C | 2.9 ^{b, c} |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | °C |
| Soldering recommendations (peak temperature) ^c | | 260 | |

THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | TYPICAL | MAXIMUM | UNIT |
|--|------------|---------|---------|------|
| Maximum junction-to-ambient ^b | R_{thJA} | 15 | 30 | °C/W |
| Maximum junction-to-case (drain) | R_{thJC} | 0.8 | 1.2 | |
| Maximum junction-to-case (source) | R_{thJC} | 1.0 | 1.5 | |

Notes:

- Based on $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Calculated based on maximum junction temperature.

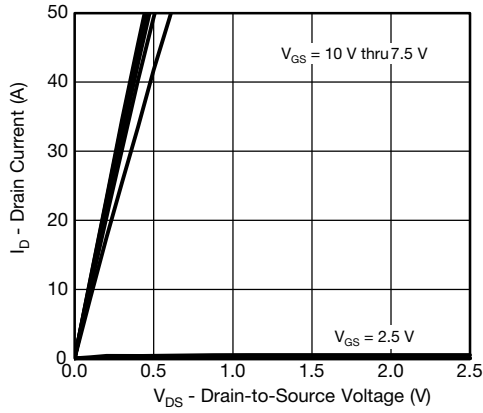
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|-------------------------|--|------|-------|-------|----------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 120 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | - | 56 | - | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ temperature coefficient | $\Delta V_{GS(th)}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | - | -6 | - | |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1 | - | 4 | V |
| Gate-source leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | - | - | 100 | nA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | - | - | 1 | μA |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$ | - | - | 10 | |
| On-state drain current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 85 | - | - | A |
| Drain-source on-state resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | - | 0.008 | 0.010 | Ω |
| Forward transconductance ^a | g_{fs} | $V_{DS} = 10\text{ V}, I_D = 20\text{ A}$ | - | 60 | - | S |
| Dynamic ^b | | | | | | |
| Input capacitance | C_{iss} | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | - | 7010 | - | μF |
| Output capacitance | C_{oss} | | - | 1610 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 186 | - | |
| Total gate charge | Q_g | $V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | - | 79 | - | nC |
| Gate-source charge | Q_{gs} | | - | 11 | - | |
| Gate-drain charge | Q_{gd} | | - | 7 | - | |
| Output charge | Q_{oss} | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$ | - | 30 | - | |
| Gate resistance | R_g | $f = 1\text{ MHz}$ | 0.4 | 1.2 | 2 | Ω |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, R_L = 2.5\text{ }\Omega, I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | - | 16 | - | ns |
| Rise time | t_r | | - | 22 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 45 | - | |
| Fall time | t_f | | - | 10 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous source-drain diode current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | - | - | 85 | A |
| Pulse diode forward current ($t_p = 100\text{ }\mu\text{s}$) | I_{SM} | | - | - | 340 | |
| Body diode voltage | V_{SD} | $I_S = 5\text{ A}, V_{GS} = 0\text{ V}$ | - | 0.7 | 1.2 | V |
| Body diode reverse recovery time | t_{rr} | $I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | - | 55 | 112 | ns |
| Body diode reverse recovery charge | Q_{rr} | | - | 72 | 137 | nC |
| Reverse recovery fall time | t_a | | - | 25 | - | ns |
| Reverse recovery rise time | t_b | | - | 20 | - | |

Notes

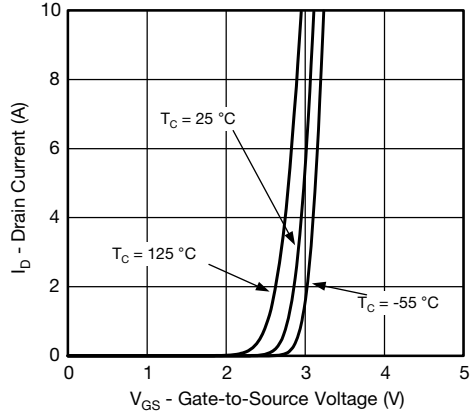
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

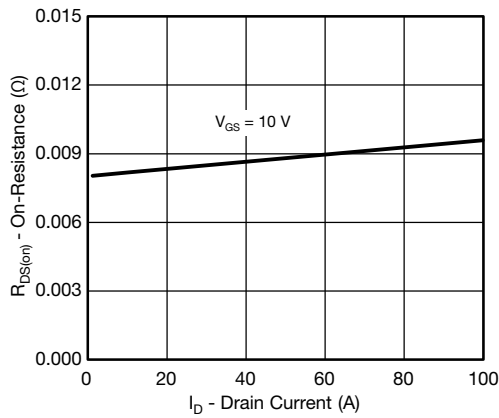
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



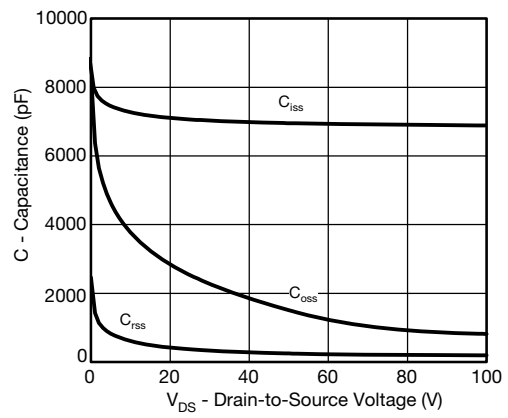
Output Characteristics



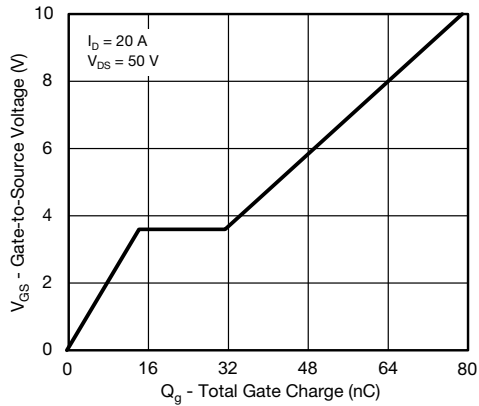
Transfer Characteristics



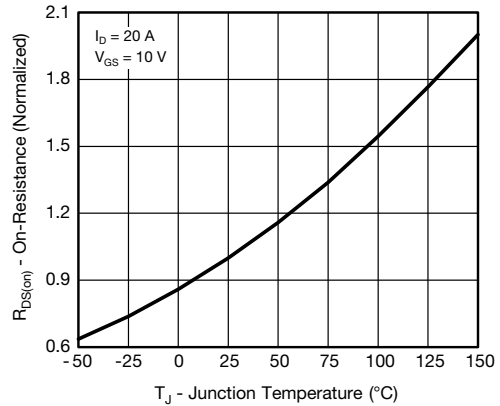
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

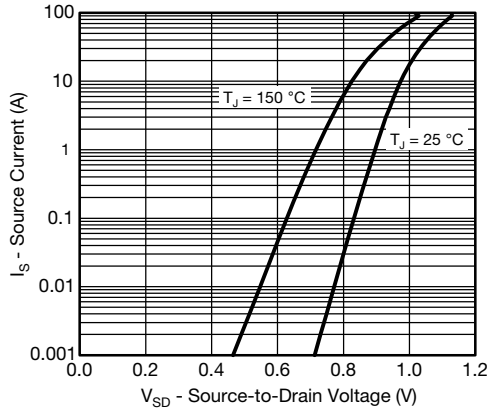


Gate Charge

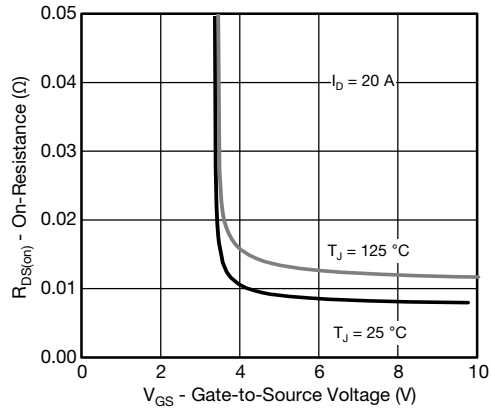


On-Resistance vs. Junction Temperature

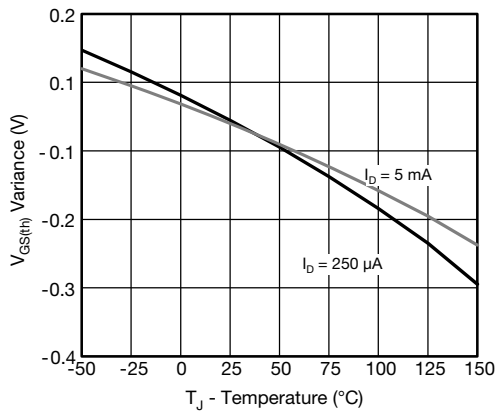
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



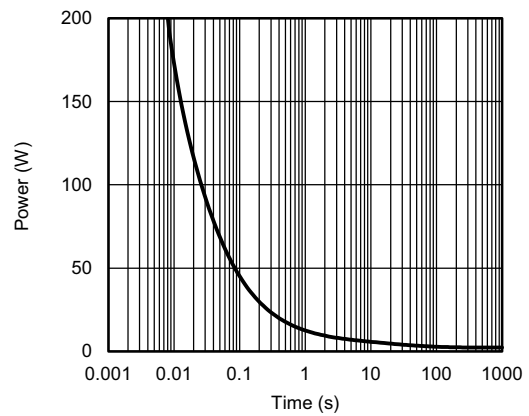
Source-Drain Diode Forward Voltage



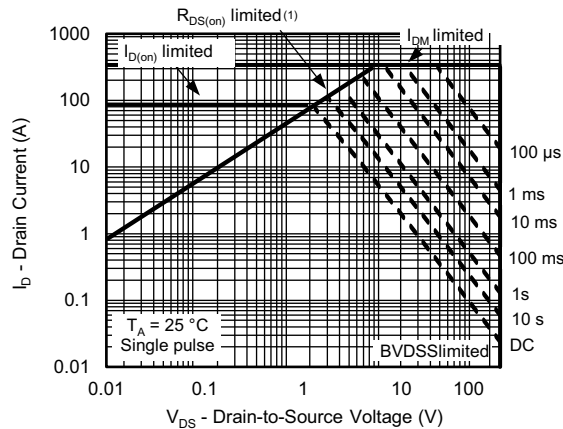
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



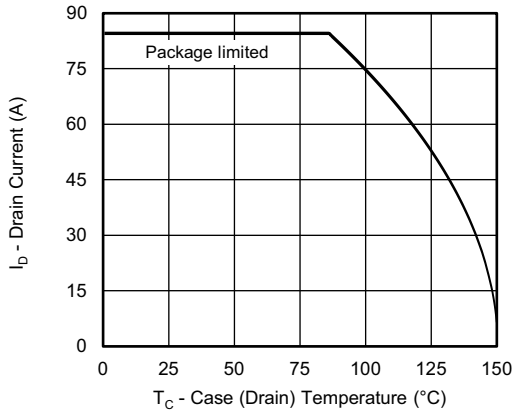
Single Pulse Power, Junction-to-Ambient



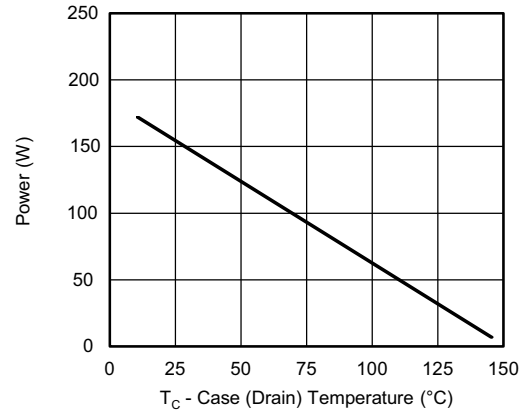
(1) $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a

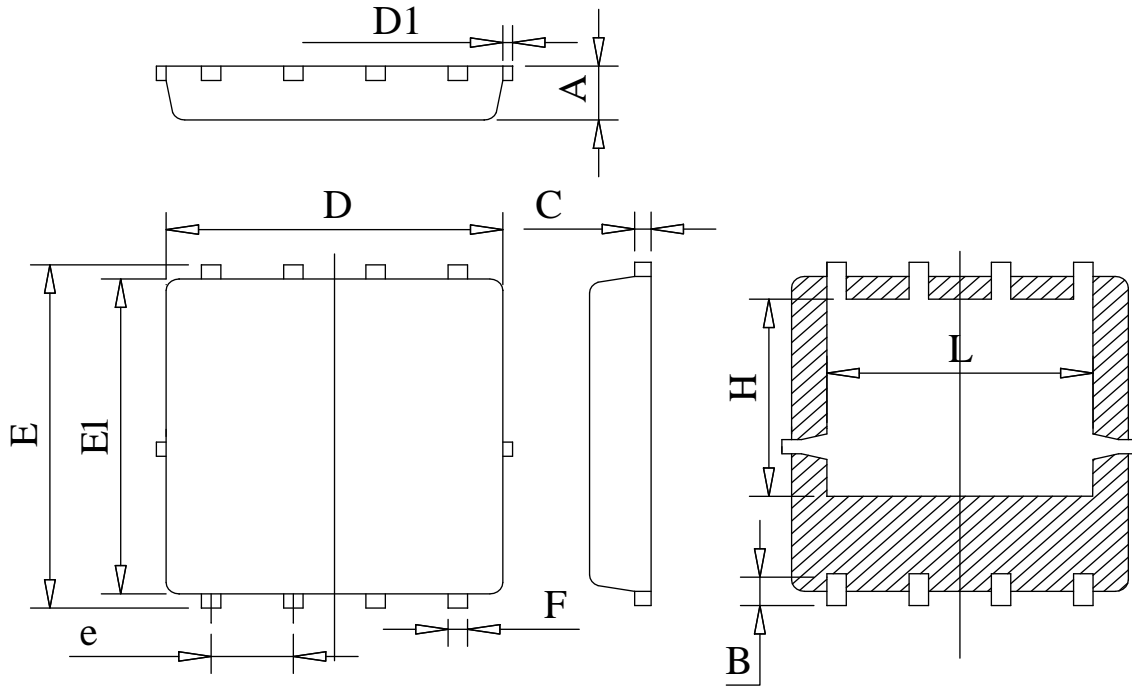


Power, Junction-to-Case

Note

- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Unit : mm

| Symbol | Min | Typ | Max |
|--------|------|-------|------|
| A | 0.78 | 0.95 | 1.12 |
| B | 0.45 | 0.58 | 0.78 |
| C | 0.18 | 0.254 | 0.36 |
| D | 4.70 | 5.20 | 5.45 |
| D1 | | | 0.18 |
| E | 5.85 | 6.05 | 6.25 |
| E1 | 5.38 | 5.55 | 5.98 |
| e | 1.15 | 1.27 | 1.40 |
| F | 0.18 | 0.30 | 0.52 |
| H | 3.25 | 3.47 | 3.70 |
| L | 3.75 | 4.00 | 4.25 |

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